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MICROWAVE THEORY AND TECHNIQUES SOCIETY

August 1982

THE IEEE
TRANSACTIONS ON MICROWAVE THEORY AND TECHNIQUES

Will Publish a
Special Issue
on

POWER AND LOW-NOISE GaAs FET CIRCUITS AND APPLICATIONS

Scheduled for March 1984

Considerable progress has been made over the past several years in power and low-noise GaAs FETs and circuits. Power FETs with output powers of 20-30 watts at S-C bands and few hundred milliwatts at K-band have been reported. Super low-noise FETs operating at EHF frequencies have achieved encouraging results. Increasing interest in the GaAs monolithic IC technology has also impacted the device/circuit improvement. The purpose of this special issue is to cover new developments and state-of-the-art results of hybrid and monolithic power and low-noise GaAs FET circuits and applications.

Papers describing original work in the following (but not limited to) areas relating to both discrete and monolithic GaAs FET circuit technology and applications are solicited:

- o Broadband Amplifier Design Techniques
- o Power Combining
- o High-Frequency Circuits
- o Dual-Gate FET Circuits
- o Low-Noise FET Characterization Techniques
- o Low-Noise Receiver
- o Amplifier and Oscillator Characterization
- o Oscillators
- o Large-Signal Load Pulling
- o Novel FET Circuits

For further information contact the Guest Editors of the Special Issue.

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All manuscripts should be sent to H. Q. Tserng at the above address and should arrive by the deadline.